

N-channel SiC power MOSFET

V_{DSS}	1200V
R _{DS(on)} (Typ.)	18mΩ
I _D ^{*1}	81A
P_D	312W

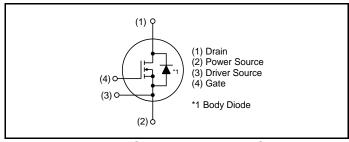
●Outline



Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Type	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT4018KR

• Absolute maximum ratings $(T_c = 25^{\circ}C)$

	,			
Parameter	Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	1200	V
Continuous drain and source current	V - V	, , *1	81	Α
$T_c = 100$ °C	$V_{GS} = V_{GS_on}$	I _D , I _S *1	57	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	l _{D,pulse} *2	179	А
Body diode pulsed forward current	$V_{GS} = 0 V$	I _{S,pulse} *3	81	А
Body diode surge forward current	$V_{GS} = 0 V$	I _{S,pulse} *4	179	А
Gate - source voltage (DC)		V_{GSS}	-4 to +21	V
Gate - source surge voltage (t _{surge} < 300ns)		${\sf V}_{\sf GSS_surge}^{*5}$	-4 to +23	V
Recommended turn-on gate - source drive voltage		$V_{\rm GS_on}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V
Virtual junction temperature		T_{vj}	175	°C
Range of storage temperature		T_{stg}	-40 to +175	°C

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values	Unit	
- raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown	\/	$V_{GS} = 0 \text{ V}, I_D = 18.6 \text{mA}$				V
voltage	$V_{(BR)DSS}$	$T_{vj} = 25^{\circ}C$	1200	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 1200 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	T _{vj} = 25°C	-	1	80	μΑ
Diam current		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V , V_{DS} = 0V$	1	-	100	nA
Gate - Source leakage current		$V_{GS} = -4V$, $V_{DS} = 0V$	ı	-	-100	nA
Gate threshold voltage	$V_{GS (th)}^{*7}$	$V_{DS} = 10V, I_D = 22.2mA$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 42A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	18.0	23.4	mΩ
		T _{vj} = 150°C	-	36.0	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	1	-	Ω

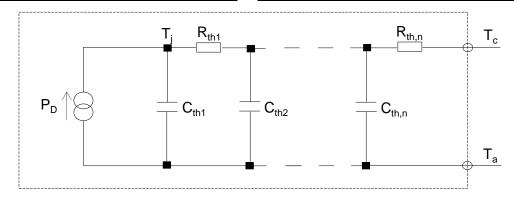
●Thermal resistance

Parameter	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC} *9	-	0.37	0.48	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.1 ×10 ⁻¹	
R _{th2}	1.3 ×10 ⁻¹	K/W
R _{th3}	1.3 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	7.8 ×10 ⁻⁴	
C _{th2}	3.1 × 10 ⁻³	Ws/K
C _{th3}	3.8 × 10 ⁻³	



Electrical characteristics ($T_{vj} = 25$ °C unless otherwise specified)

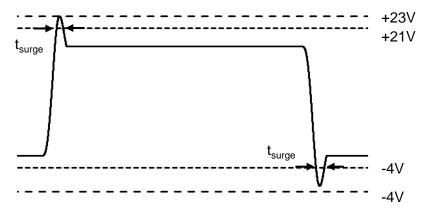
Doromotor	Symbol Conditions	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g fs *8	$V_{DS} = 10V, I_{D} = 42A$	-	29	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	4532	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	129	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	9	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 800V$	ı	156	-	pF
Total Gate charge	Q _g *8	$V_{DS} = 800V$ $I_{D} = 42A$	-	170	ı	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	-	32	ı	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	52	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 800V$ $I_{D} = 42A$	-	13	-	
Rise time	t _r *8	$V_{GS} = +18V / 0V$	-	21	-	200
Turn - off delay time	t _{d(off)} *8	$R_G = 3.3\Omega$, L = 250µH E_{on} includes diode	-	50	-	ns
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	11	-	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	520	-	1
Turn - off switching loss	E _{off} *8		-	142	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values	Unit	
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_D = 42A$	ı	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 42A$ $V_R = 800V$	ı	12	1	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 4700A/µs	ı	252	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	44	-	А

^{*1} Limited by maximum T_{vi} and for Max. R_{thJC} .

^{*5} Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

- * 6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

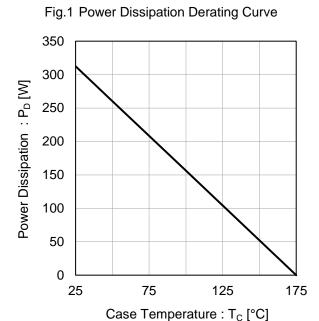
 $URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf$

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^{*2} $P_W \le 10\mu s$, Duty cycle $\le 1\%$

^{*3} Only for body-diode, Repititive pulse, PW ≤ 500ns, Duty cycle ≤ 5%

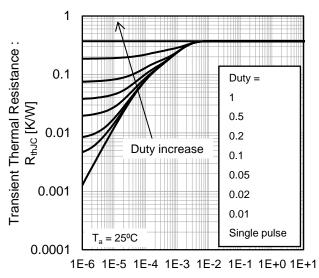
^{*4} When used as a protective function, PW \leq 10 μ s



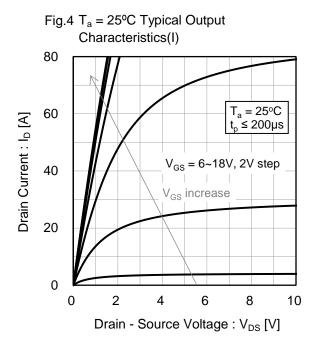
1000 Operation in this area is limited by R_{DS(on)} P_W 100 Drain Current: Ip [A] <100ns* 1µs* 10 10µs* PW decrease 100µs 1 1ms $T_a = 25^{\circ}C$ Single Pulse *Calculation(P_W≤10µs) 10ms 0.1 0.1 10 100 1000 10000 Drain - Source Voltage: V_{DS} [V]

Fig.2 Maximum Safe Operating Area

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



Pulse Width: Pw [s]



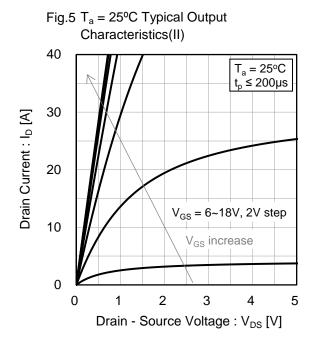
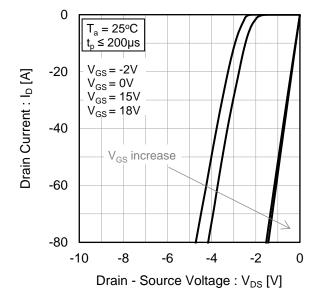
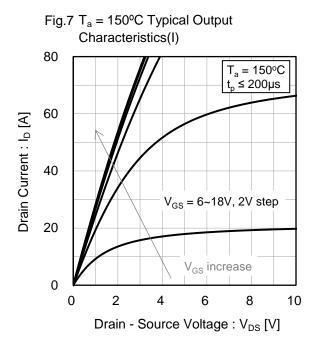
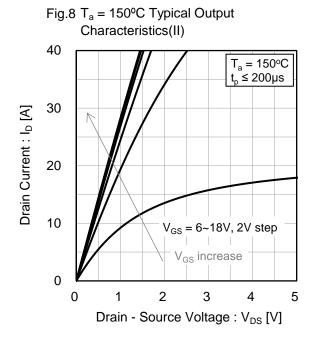
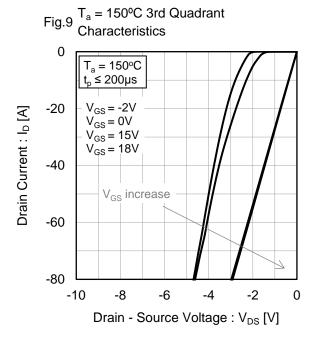


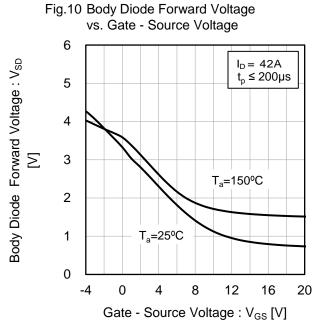
Fig.6 T_a = 25°C 3rd Quadrant Characteristics











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Fig.11 Typical Transfer Characteristics (I)

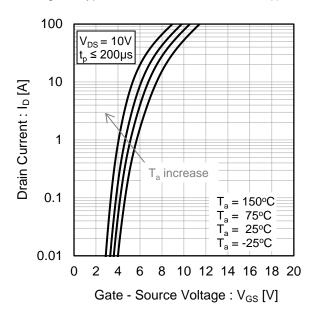


Fig.12 Typical Transfer Characteristics (II)

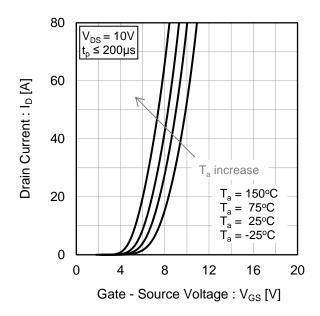


Fig.13 Gate Threshold Voltage vs. Junction Temperature

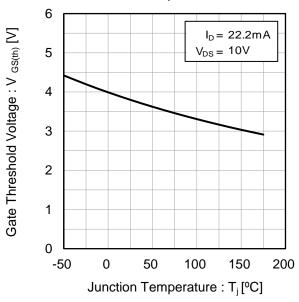


Fig.14 Transconductance vs. Drain Current

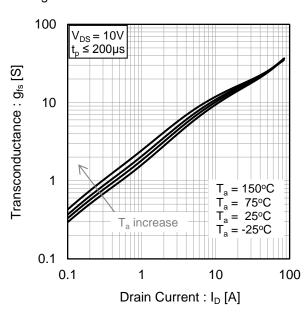


Fig.15 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

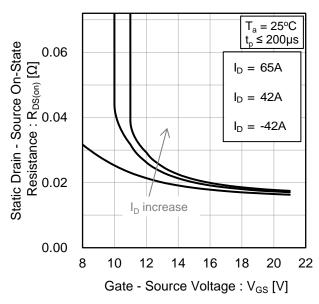


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

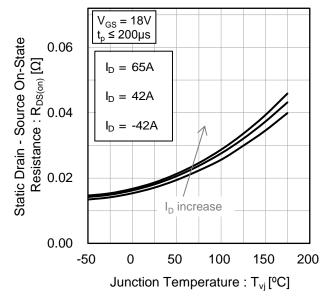


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

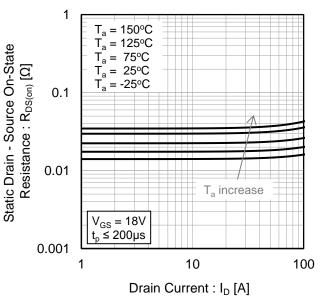
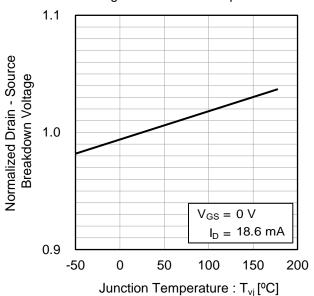
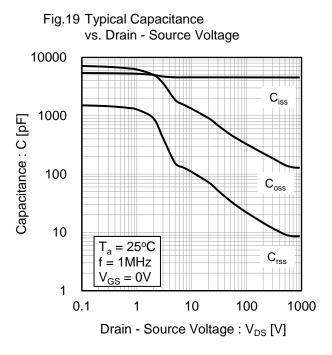


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Junction Temperature





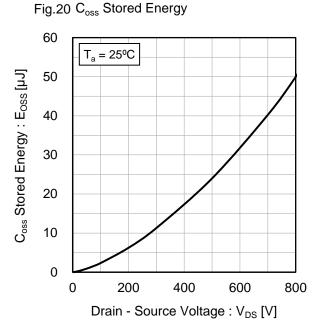


Fig.21 Dynamic Input Characteristics

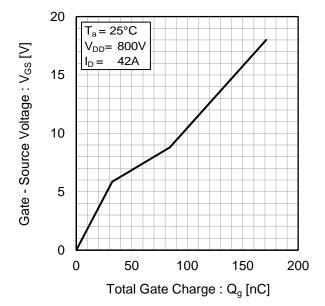


Fig.22 Typical Switching Time vs. External Gate Resistance 250 25°C 42A $I_D =$ V_{DD}= 800V 200 V_{GS}= +18V/0V $t_{d(off)}$ Switching Time: t [ns] 250µH 150 100 $t_{d(on)}$ ¦ t_r 50 0

10

External Gate Resistance : R_G [Ω]

15

20

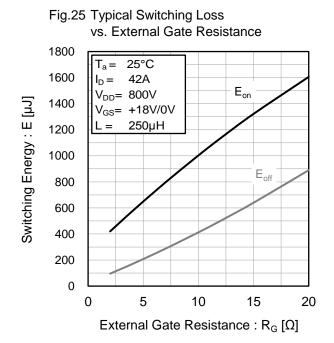
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vs. Drain - Source Voltage 1800 25°C 1600 42A V_{GS}= +18V/0V Switching Energy : E [µJ] 1400 $R_G = 3.3\Omega$ 250µH 1200 1000 800 600 E_{on} 400 200 0 400 200 600 800 Drain - Source Voltage: V_{DS} [V]

Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 1800 25°C 1600 $V_{DD} = 800V$ $V_{GS} =$ +18V/0V Switching Energy: E [µJ] 1400 3.3Ω $R_G =$ 1200 250µH 1000 E_{on} 800 600 $\mathsf{E}_{\mathsf{off}}$ 400 200 0 0 20 40 60 80 Drain Current: I_D [A]



•Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

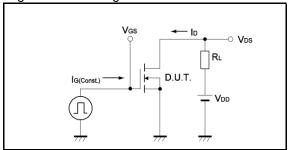


Fig.2-1 Switching Characteristics Measurement Circuit

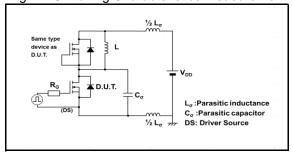


Fig.2-3 Waveforms for Switching Energy Loss

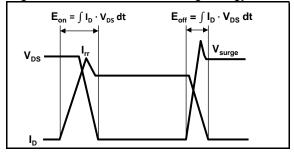


Fig.3-1 Reverse Recovery Time Measurement Circuit

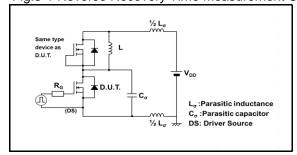


Fig.1-2 Gate Charge Waveform

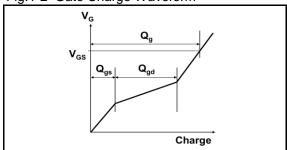


Fig.2-2 Waveforms for Switching Time

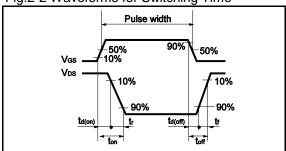
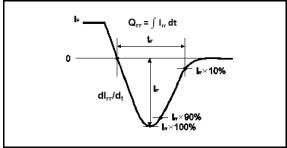
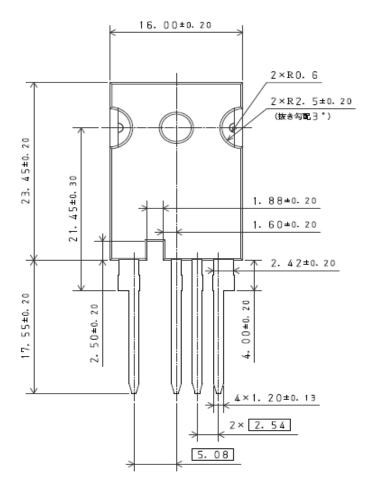
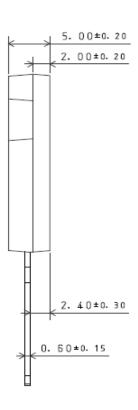


Fig.3-2 Reverse Recovery Waveform

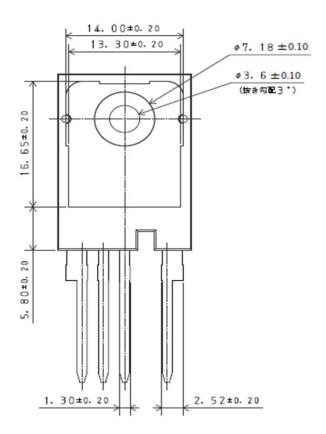


Package Dimensions



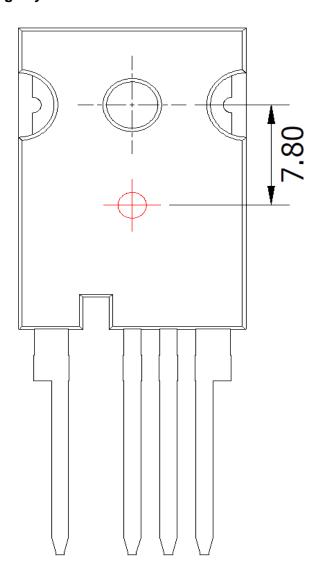


Unit: mm



Unit: mm

●Die Bonding Layout



- •Front view of the packaging.
- ·Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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